

IN THE CLAIMS

Claims 1-30 (Canceled)

31. (Previously Presented) A method of manufacturing a semiconductor device comprising the steps of:

providing a film substrate having a main surface, a rear surface opposing to the main surface, a plurality of device forming areas of the main surface and electrode members individually separated from one another and formed on the device forming areas;

providing a plurality of semiconductor chips each having a main surface and electrodes formed on the main surface thereof;

arranging the semiconductor chips on respective ones of the device forming areas and electrically connecting the electrodes of the semiconductor chips with electrode members on the respective device forming areas;

forming a resin encapsulator collectively sealing the plurality of device forming areas, the electrode members and the semiconductor chips; and

separating the resin encapsulator from the film substrate and thereby revealing the electrode members on one side of the resin encapsulator;

wherein the electrode members are spaced from a side surface of the resin encapsulator.

Claim 32 (Canceled)

33. (Currently Amended) A method of manufacturing a semiconductor device according to claim 31, further comprising a step of cutting the resin encapsulator and the film substrate between adjacent device forming areas by dicing, after the forming step, wherein the cutting step includes a step of sticking dicing tape on another side of the resin encapsulator, wherein the another side is opposed to the one side of the resin encapsulator.

34. (Previously Presented) A method of manufacturing a semiconductor device according to claim 31, further comprising a step of plating the revealed electrode members, after the step of separating the resin encapsulator.

35. (Currently Amended) A method of manufacturing a semiconductor device according to claim 34, further comprising a step of cutting the resin encapsulator and the film substrate between adjacent device forming areas by dicing,

after the forming step, wherein the plating step is performed before the cutting step.

36. (Previously Presented) A method of manufacturing a semiconductor device according to claim 31, wherein the film substrate comprises a resin sheet having an adhesive layer on one main surface, and wherein the semiconductor chip and the plurality of electrode members are fixed to the substrate by the adhesive layer.

37. (Previously Presented) A method of manufacturing a semiconductor device according to claim 33, wherein the film substrate comprises a resin sheet having an adhesive layer on one main surface, and wherein the semiconductor chip and the plurality of electrode members are fixed to the substrate by the adhesive layer.

38. (Previously Presented) A method of manufacturing a semiconductor device according to claim 34, wherein the film substrate comprises a resin sheet having an adhesive layer on one main surface, and wherein the semiconductor chip and the plurality of electrode members are fixed to the substrate by the adhesive layer.

39. (Previously Presented) A method of manufacturing a semiconductor device according to claim 35, wherein the film substrate comprises a resin sheet having an adhesive layer on one main surface, and wherein the semiconductor chip and the plurality of electrode members are fixed to the substrate by the adhesive layer.